LM324-MIL 四路运算放大器

1 特性

- 宽电源范围
  – 单电源：3V 至 32V
  – 双电源：±1.5V 至 ±16V
- 独立于
  电源电压的低电源电流漏极：0.8mA（典型值）
- 共模输入电压范围包括接地，允许近地直接感应
- 低输入偏置和偏移参数
  – 输入偏移电压：3mV（典型值）
  – 输入偏移电流：2nA（典型值）
  – 输入偏置电流：20nA（典型值）
- 差分输入电压范围等于最大额定电源电压：
  32V
- 开环差分电压放大：
  100V/mV（典型值）
- 内部频率补偿
- 对于符合 MIL-PRF-38535 标准的产品，
  除非另外注明，否则会测试所有参数。对于所有其他产品，生产流程不一定包括所有参数的测试。

2 应用

- 蓝光播放器和家庭影院
- 化学和气体传感器
- DVD 录像机和播放器
- 数字万用表：工作台和系统
- 数字万用表：手持设备
- 场发射器：温度传感器
- 电机控制：交流感应、刷式直流、无刷直流、高电压、低电压、永久磁性和步进电机
- 示波器
- 电视：LCD 和数字
- 采用 Modbus 的温度传感器或控制器
- 磅秤

3 说明

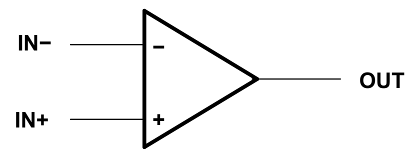
该器件包含四个独立的高增益频率补偿运算放大器，专为在宽电压范围内使用单电源而设计。

器件信息[(1)]

器件型号	封装	封装尺寸（标称值）
LM324-MIL	SOIC (14)	8.65mm x 3.91mm
	CDIP (14)	19.56mm × 6.67mm
	PDIP (14)	19.30mm x 6.35mm
	CFP (14)	9.21mm × 5.97mm
	薄型小外形尺寸封装 (TSSOP) (14)	5.00mm x 4.40mm
	SO (14)	9.20mm × 5.30mm
	SSOP (14)	6.20mm x 5.30mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

符号（每个放大器）



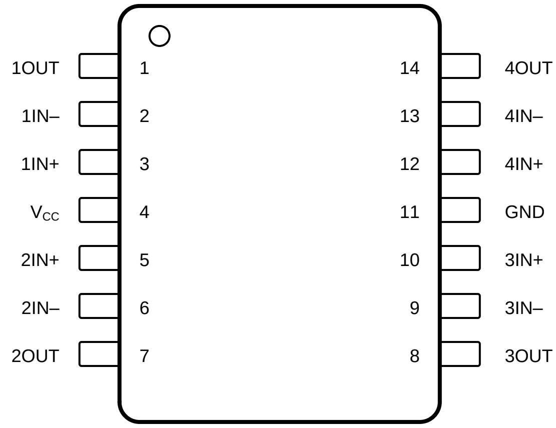
目录

4 修订历史记录

日期	修订版本	注意
2017 年 6 月	*	初始发行版。

5 Pin Configuration and Functions

D, DB, J, N, NS, PW, W PACKAGE
14-Pin SOIC, SSOP, CDIP, PDIP, SO, TSSOP, CFP
(Top View)



Not to scale

Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
1IN–	2	I	Negative input
1IN+	3	I	Positive input
1OUT	1	O	Output
2IN–	6	I	Negative input
2IN+	5	I	Positive input
2OUT	7	O	Output
3IN–	9	I	Negative input
3IN+	10	I	Positive input
3OUT	8	O	Output
4IN–	13	I	Negative input
4IN+	12	I	Positive input
4OUT	14	O	Output
GND	11	—	Ground
NC	—	—	Do not connect
V_{CC}	4	—	Power supply

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
Supply voltage, V_{CC} (2)		±16	32	V
Differential input voltage, V_{ID} (3)			±32	V
Input voltage, V_I (either input)		–0.3	32	V
Duration of output short circuit (one amplifier) to ground at (or below) T_A = 25°C, V_{CC} ≤ 15 V (4)		Unlimited		
Operating virtual junction temperature, T_J			150	°C
Case temperature for 60 seconds	FK package		260	°C
Storage temperature, T_{stg}		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltage values (except differential voltages and V_{CC} specified for the measurement of I_{OS}) are with respect to the network GND.
(3) Differential voltages are at IN+, with respect to IN−.
(4) Short circuits from outputs to VCC can cause excessive heating and eventual destruction.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	±500	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101	±1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V_{CC}	Supply voltage	3	30	V
V_{CM}	Common-mode voltage	0	V_{CC} – 2	V
T_A	Operating free air temperature	0	70	°C

6.4 Thermal Information

THERMAL METRIC (1)		D (SOIC)	DB (SSOP)	N (PDIP)	NS (SO)	PW (TSSOP)	J (CDIP)	W (CFP)	UNIT
		14 PINS	14 PINS	14 PINS	14 PINS	14 PINS	14 PINS	14 PINS	
$R_{\theta JA}$ (2)(3)	Junction-to-ambient thermal resistance	86	86	80	76	113	—	—	°C/W
$R_{\theta JC}$ (4)	Junction-to-case (top) thermal resistance	—	—	—	—	—	15.05	14.65	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.
(2) Short circuits from outputs to VCC can cause excessive heating and eventual destruction.
(3) Maximum power dissipation is a function of $T_{J(max)}$, $R_{\theta JA}$, and T_A. The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_{J(max)} – T_A)/R_{\theta JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.
(4) Maximum power dissipation is a function of $T_{J(max)}$, $R_{\theta JA}$, and T_C. The maximum allowable power dissipation at any allowable case temperature is $P_D = (T_{J(max)} – T_C)/R_{\theta JC}$. Operating at the absolute maximum T_J of 150°C can affect reliability.

6.5 Electrical Characteristics

at specified free-air temperature, V_{CC} = 5 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS(1)		T_A(2)	MIN	TYP(3)	MAX	UNIT
V_{IO}	Input offset voltage	V_{CC} = 5 V to MAX, V_{IC} = V_{ICR}min, V_O = 1.4 V		25°C		3	7	mV
				Full range			9	
I_{IO}	Input offset current	V_O = 1.4 V		25°C		2	50	nA
				Full range			150	
I_{IB}	Input bias current	V_O = 1.4 V		25°C		–20	–250	nA
				Full range			–500	
V_{ICR}	Common-mode input voltage range	V_{CC} = 5 V to MAX		25°C	0 to V_{CC} – 1.5			V
				Full range	0 to V_{CC} – 2			
V_{OH}	High-level output voltage	R_L = 2 kΩ		25°C	V_{CC} – 1.5			V
		R_L = 10 kΩ		25°C				
		V_{CC} = MAX	R_L = 2 kΩ	Full range	26			
			R_L ≥ 10 kΩ	Full range	27	28		
V_{OL}	Low-level output voltage	R_L ≤ 10 kΩ		Full range		5	20	mV
A_{VD}	Large-signal differential voltage amplification	V_{CC} = 15 V, V_O = 1 V to 11 V, R_L ≥ 2 kΩ		25°C	25	100		V/mV
				Full range	15			
CMRR	Common-mode rejection ratio	V_{IC} = V_{ICR}min		25°C	65	80		dB
k_{SVR}	Supply-voltage rejection ratio (ΔV_{CC} /ΔVIO)			25°C	65	100		dB
V_{O1}/ V_{O2}	Crosstalk attenuation	f = 1 kHz to 20 kHz		25°C		120		dB
I_O	Output current	V_{CC} = 15 V, V_{ID} = 1 V, V_O = 0	Source	25°C	–20	–30	–60	mA
				Full range	–10			
		V_{CC} = 15 V, V_{ID} = –1 V, V_O = 15 V	Sink	25°C	10	20		
				Full range	5			
		V_{ID} = –1 V, V_O = 200 mV		25°C	12	30		μA
I_{OS}	Short-circuit output current	V_{CC} at 5 V, V_O = 0, GND at –5 V		25°C		±40	±60	mA
I_{CC}	Supply current (four amplifiers)	V_O = 2.5 V, no load		Full range		0.7	1.2	mA
		V_{CC} = MAX, V_O = 0.5 V_{CC}, no load		Full range		1.4	3	

(1) All characteristics are measured under open-loop conditions, with zero common-mode input voltage, unless otherwise specified. MAX V_{CC} for testing purposes is 30 V.
(2) Full range is 0°C to 70°C for LM324-MIL.
(3) All typical values are at T_A = 25°C

6.6 Operating Conditions

V_{CC} = ±15 V, T_A = 25°C

PARAMETER		TEST CONDITIONS	TYP	UNIT
SR	Slew rate at unity gain	R_L = 1 MΩ, C_L = 30 pF, V_I = ±10 V (see Figure 7)	0.5	V/μs
B_1	Unity-gain bandwidth	R_L = 1 MΩ, C_L = 20 pF (see Figure 7)	1.2	MHz
V_n	Equivalent input noise voltage	R_S = 100 Ω, V_I = 0 V, f = 1 kHz (see Figure 8)	35	nV/√Hz

6.7 Typical Characteristics

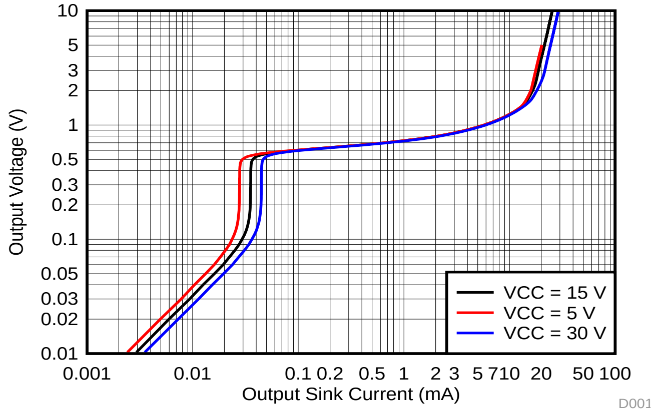


Figure 1. Output Sinking Characteristics

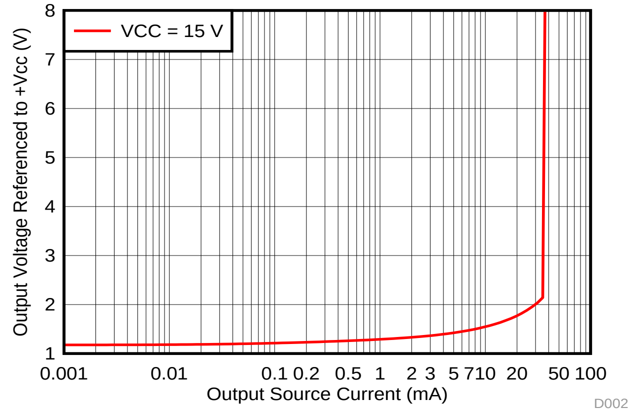


Figure 2. Output Sourcing Characteristics

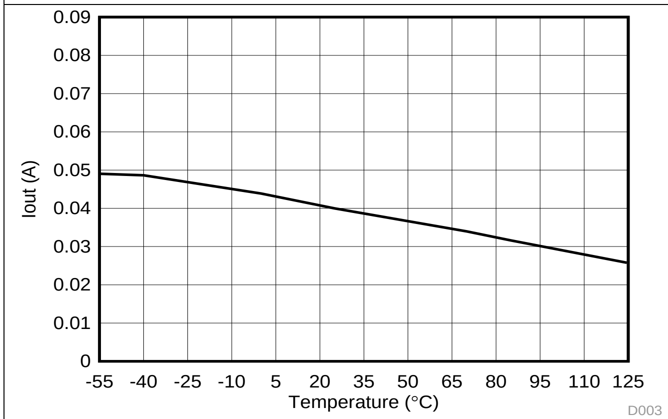


Figure 3. Source Current Limiting

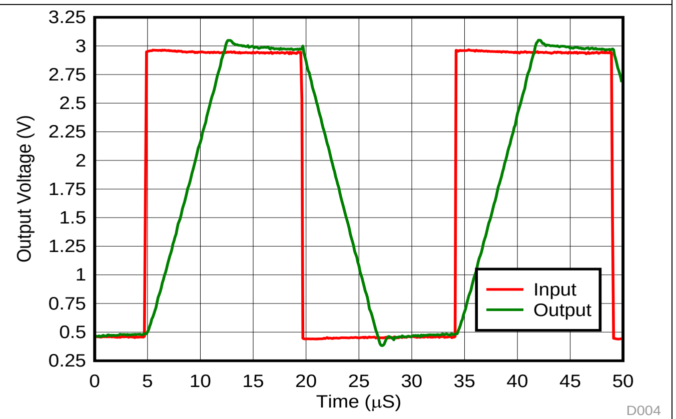


Figure 4. Voltage Follower Large Signal Response (50 pF)

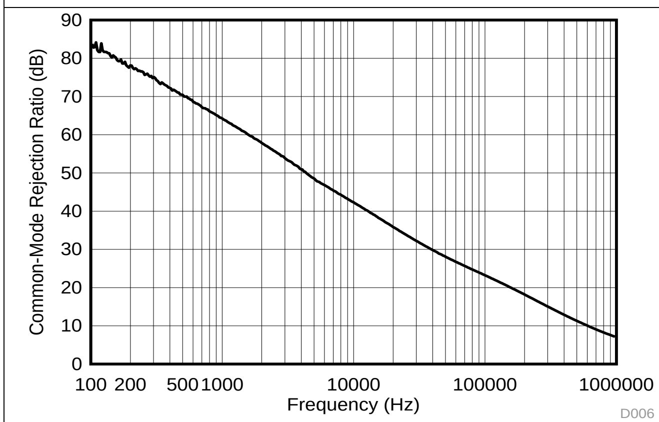


Figure 5. Common-Mode Rejection Ratio

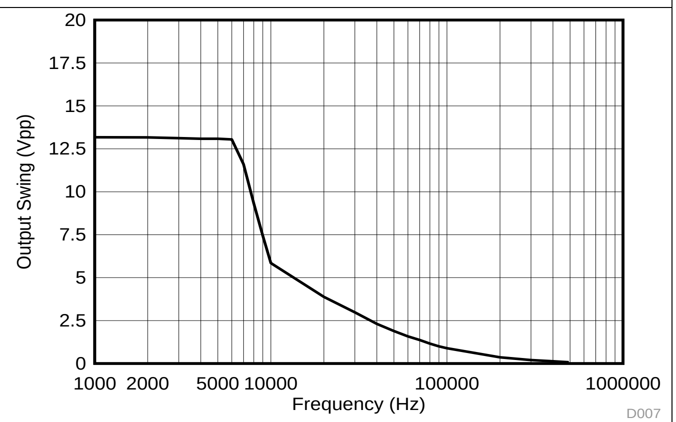


Figure 6. Maximum Output Swing vs. Frequency (VCC = 15 V)

7 Parameter Measurement Information

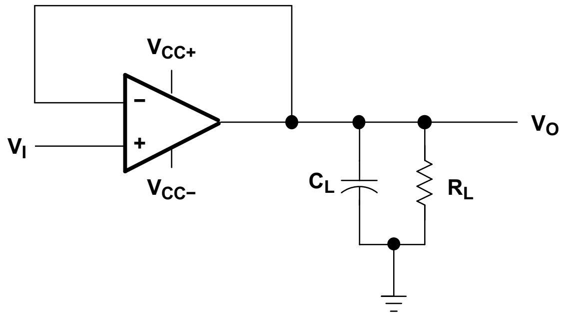


Figure 7. Unity-Gain Amplifier

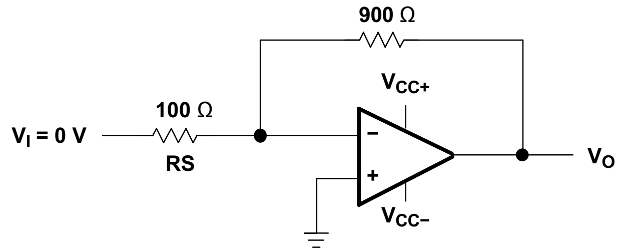


Figure 8. Noise-Test Circuit

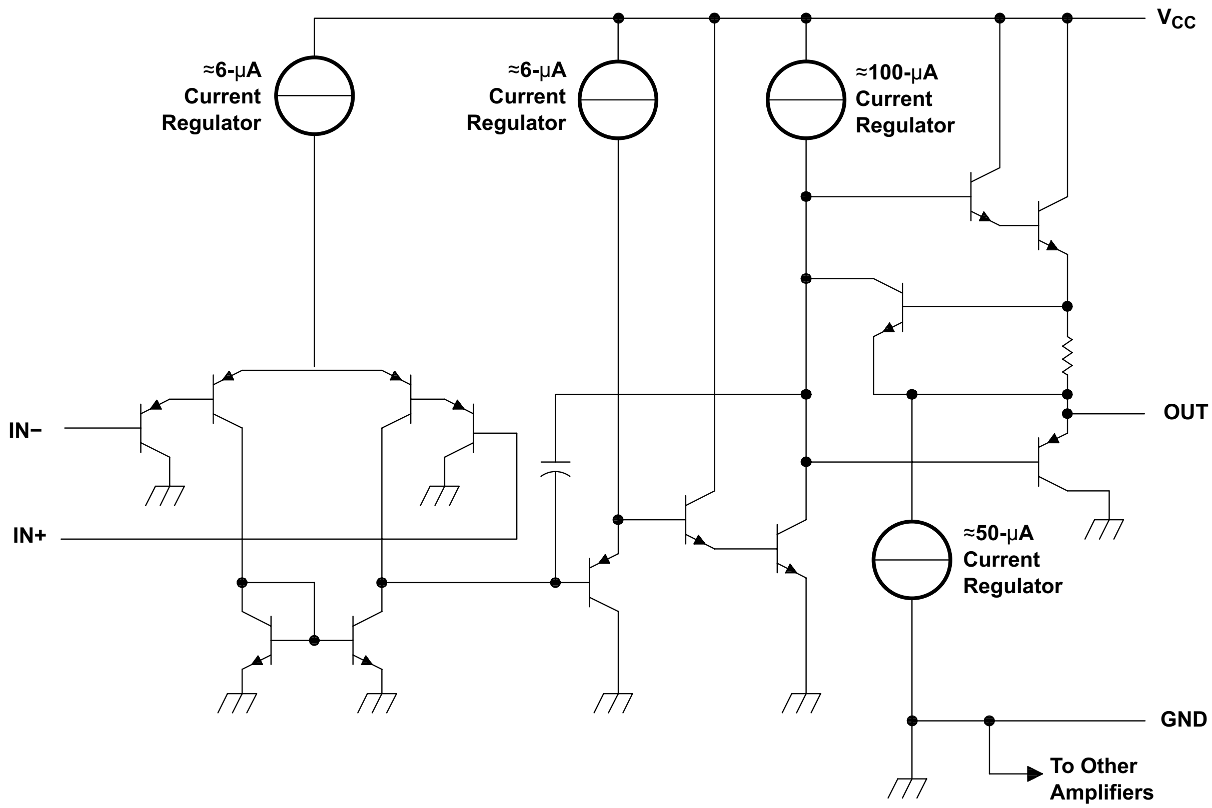
8 Detailed Description

8.1 Overview

The device consists of four independent high-gain frequency-compensated operational amplifiers that are designed specifically to operate from a single supply over a wide range of voltages. Operation from split supplies also is possible if the difference between the two supplies is 3 V to 32 V, and V_{CC} is at least 1.5 V more positive than the input common-mode voltage. The low supply-current drain is independent of the magnitude of the supply voltage.

Applications include transducer amplifiers, DC amplification blocks, and all the conventional operational-amplifier circuits that now can be more easily implemented in single-supply-voltage systems. For example, the LM324-MIL device can be operated directly from the standard 5-V supply that is used in digital systems and provides the required interface electronics, without requiring additional ±15-V supplies.

8.2 Functional Block Diagram



COMPONENT COUNT (total device)	
Epi-FET	1
Transistors	95
Diodes	4
Resistors	11
Capacitors	4

8.3 Feature Description

8.3.1 Unity-Gain Bandwidth

Gain bandwidth product is found by multiplying the measured bandwidth of an amplifier by the gain at which that bandwidth was measured. These devices have a high gain bandwidth of 1.2 MHz.

8.3.2 Slew Rate

The slew rate is the rate at which an operational amplifier can change its output when there is a change on the input. These devices have a 0.5-V/μs slew rate.

8.3.3 Input Common Mode Range

The valid common mode range is from device ground to V_{CC} – 1.5 V (V_{CC} – 2 V across temperature). Inputs may exceed V_{CC} up to the maximum V_{CC} without device damage. At least one input must be in the valid input common mode range for output to be correct phase. If both inputs exceed valid range then output phase is undefined. If either input is less than –0.3 V then input current should be limited to 1 mA and output phase is undefined.

8.4 Device Functional Modes

The device is powered on when the supply is connected. This device can be operated as a single supply operational amplifier or dual supply amplifier depending on the application.

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The LM324-MIL operational amplifier is useful in a wide range of signal conditioning applications. Inputs can be powered before VCC for flexibility in multiple supply circuits.

9.2 Typical Application

A typical application for an operational amplifier in an inverting amplifier. This amplifier takes a positive voltage on the input, and makes it a negative voltage of the same magnitude. In the same manner, it also makes negative voltages positive.

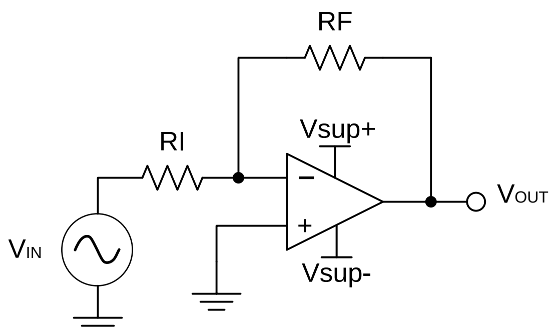


Figure 9. Application Schematic

9.2.1 Design Requirements

The supply voltage must be chosen such that it is larger than the input voltage range and output range. For instance, this application will scale a signal of ±0.5 V to ±1.8 V. Setting the supply at ±12 V is sufficient to accommodate this application.

9.2.2 Detailed Design Procedure

Determine the gain required by the inverting amplifier using Equation 1 and Equation 2:

$$A_V = \frac{VOUT}{VIN} \tag{1}$$

$$A_V = \frac{1.8}{-0.5} = -3.6 \tag{2}$$

Once the desired gain is determined, choose a value for RI or RF. Choosing a value in the kilohm range is desirable because the amplifier circuit will use currents in the milliamp range. This ensures the part will not draw too much current. This example will choose 10 kΩ for RI which means 36 kΩ will be used for RF. This was determined by Equation 3.

$$A_V = -\frac{RF}{RI} \tag{3}$$

Typical Application (continued)

9.2.3 Application Curve

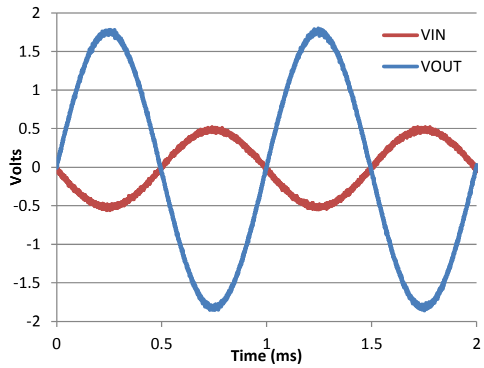


Figure 10. Input and Output Voltages of the Inverting Amplifier

10 Power Supply Recommendations

CAUTION

Supply voltages larger than 32 V for a single supply, or outside the range of ±16 V for a dual supply can permanently damage the device (see the *Absolute Maximum Ratings*).

Place 0.1-µF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high impedance power supplies. For more detailed information on bypass capacitor placement, refer to the *Layout*.

11 Layout

11.1 Layout Guidelines

For best operational performance of the device, use good PCB layout practices, including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole, as well as the operational amplifier. Bypass capacitors are used to reduce the coupled noise by providing low impedance power sources local to the analog circuitry.
  – Connect low-ESR, 0.1-μF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for single supply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most-effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces EMI noise pickup. Make sure to physically separate digital and analog grounds, paying attention to the flow of the ground current.
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If it is not possible to keep them separate, it is much better to cross the sensitive trace perpendicular as opposed to in parallel with the noisy trace.
- Place the external components as close to the device as possible. Keeping RF and RG close to the inverting input minimizes parasitic capacitance, as shown in *Layout Examples*.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.

11.2 Layout Examples

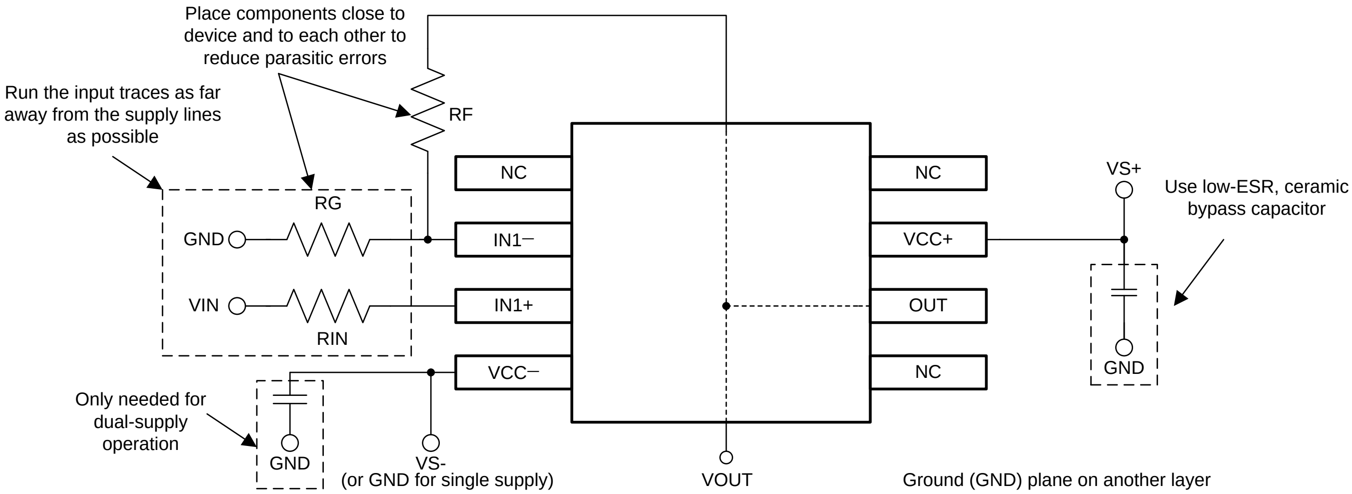


Figure 11. Operational Amplifier Board Layout for Noninverting Configuration

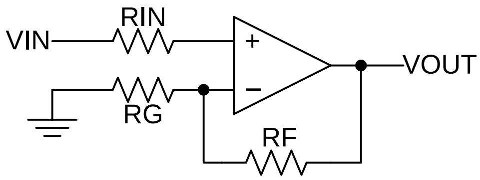


Figure 12. Operational Amplifier Schematic for Noninverting Configuration

12 器件和文档支持

12.1 文档支持

12.1.1 相关文档

相关文档如下：

《电路板布局技巧》(SLOA089)

12.2 接收文档更新通知

要接收文档更新通知，请导航至德州仪器 TI.com.cn 上的器件产品文件夹。请单击右上角的*通知我* 进行注册，即可收到任意产品信息更改每周摘要。有关更改的详细信息，请查看任意已修订文档中包含的修订历史记录。

12.3 社区资源

下列链接提供到 TI 社区资源的连接。链接的内容由各个分销商"按照原样"提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的 《使用条款》。

TI E2E™ 在线社区 ***TI 的工程师对工程师 (E2E) 社区。***此社区的创建目的在于促进工程师之间的协作。在 e2e.ti.com 中，您可以咨询问题、分享知识、拓展思路并与同行工程师一道帮助解决问题。

设计支持 ***TI 参考设计支持*** 可帮助您快速查找有帮助的 E2E 论坛、设计支持工具以及技术支持的联系信息。

12.4 商标

E2E is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

12.5 静电放电警告

这些装置包含有限的内置 ESD 保护。 存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

12.6 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 机械、封装和可订购信息

以下页中包括机械封装、封装和可订购信息。这些信息是针对指定器件可提供的最新数据。这些数据发生变化时，我们可能不会另行通知或修订此文档。要获得这份数据表的浏览器版本，请查阅左侧导航栏。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LM324 MWA	ACTIVE	WAFERSALE	YS	0	1	RoHS & Green	Call TI	Level-1-NA-UNLIM	-40 to 85		Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

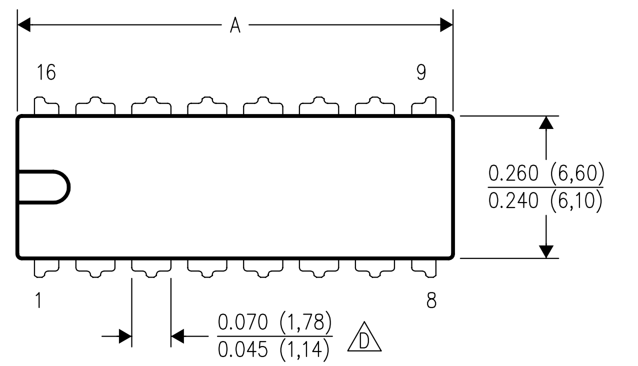
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

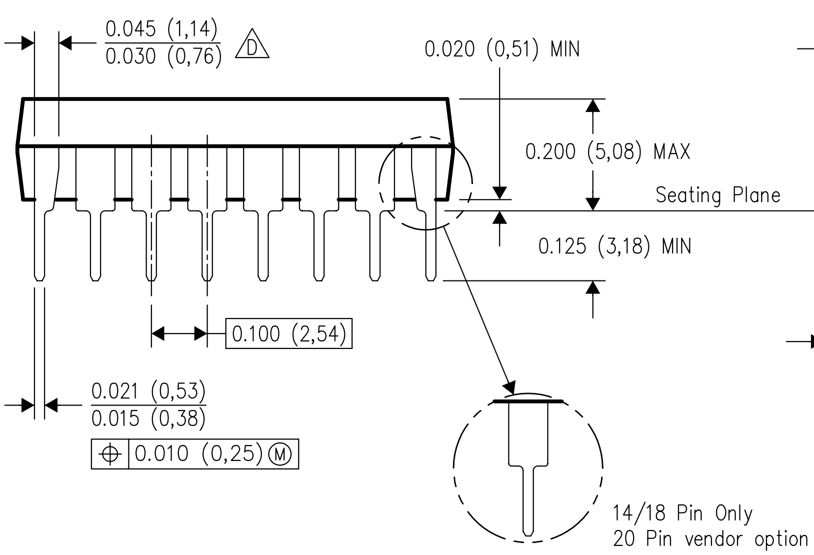
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

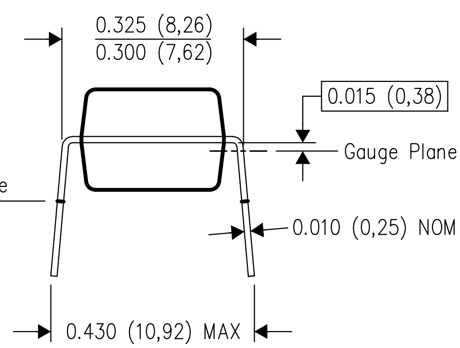
N (R–PDIP–T**) PLASTIC DUAL–IN–LINE PACKAGE

16 PINS SHOWN



DIM \ PINS **	14	16	18	20
A MAX	0.775 (19,69)	0.775 (19,69)	0.920 (23,37)	1.060 (26,92)
A MIN	0.745 (18,92)	0.745 (18,92)	0.850 (21,59)	0.940 (23,88)
MS–001 VARIATION (C)	AA	BB	AC	AD



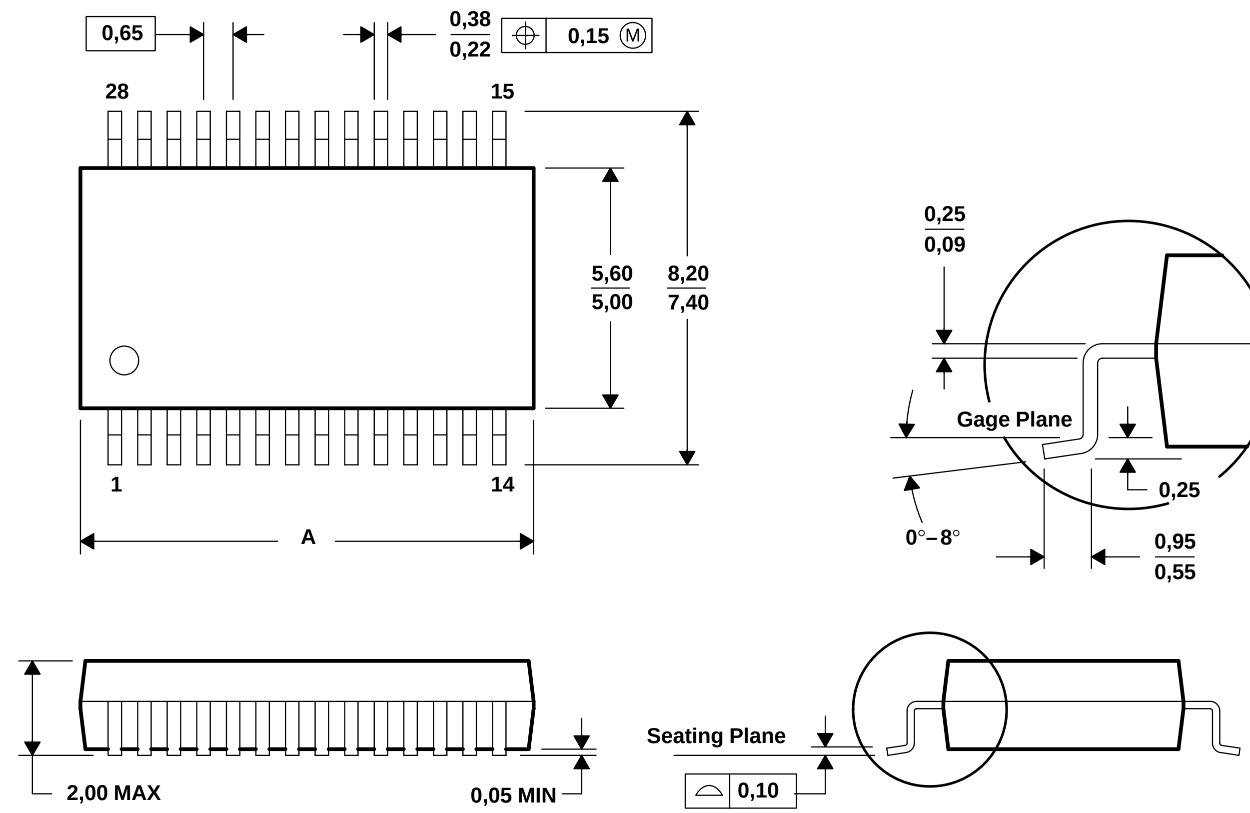


4040049/E 12/2002

NOTES:
- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- (C) Falls within JEDEC MS–001, except 18 and 20 pin minimum body length (Dim A).
- (D) The 20 pin end lead shoulder width is a vendor option, either half or full width.

DB (R-PDSO-G)** **PLASTIC SMALL-OUTLINE**

28 PINS SHOWN



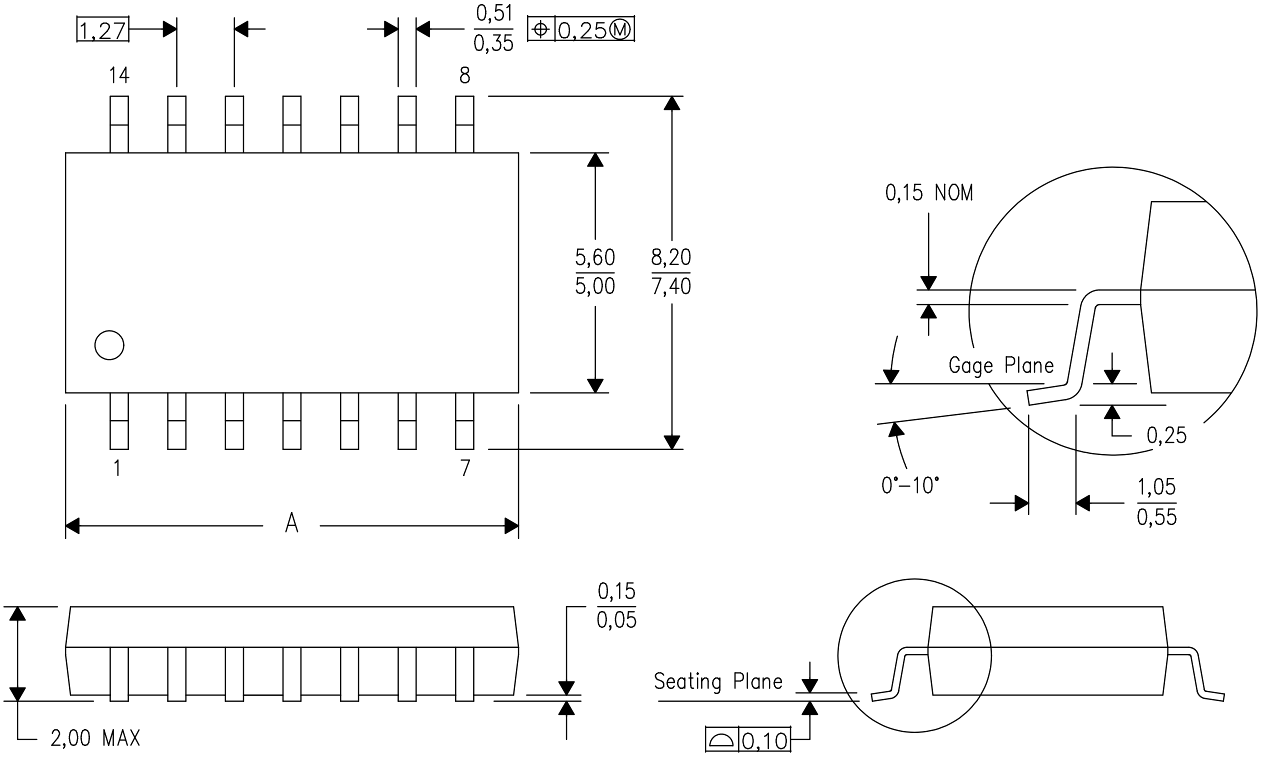
DIM \ PINS **	14	16	20	24	28	30	38
A MAX	6,50	6,50	7,50	8,50	10,50	10,50	12,90
A MIN	5,90	5,90	6,90	7,90	9,90	9,90	12,30

4040065 /E 12/01

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
D. Falls within JEDEC MO-150

NS (R-PDSO-G)** **PLASTIC SMALL-OUTLINE PACKAGE**

14-PINS SHOWN

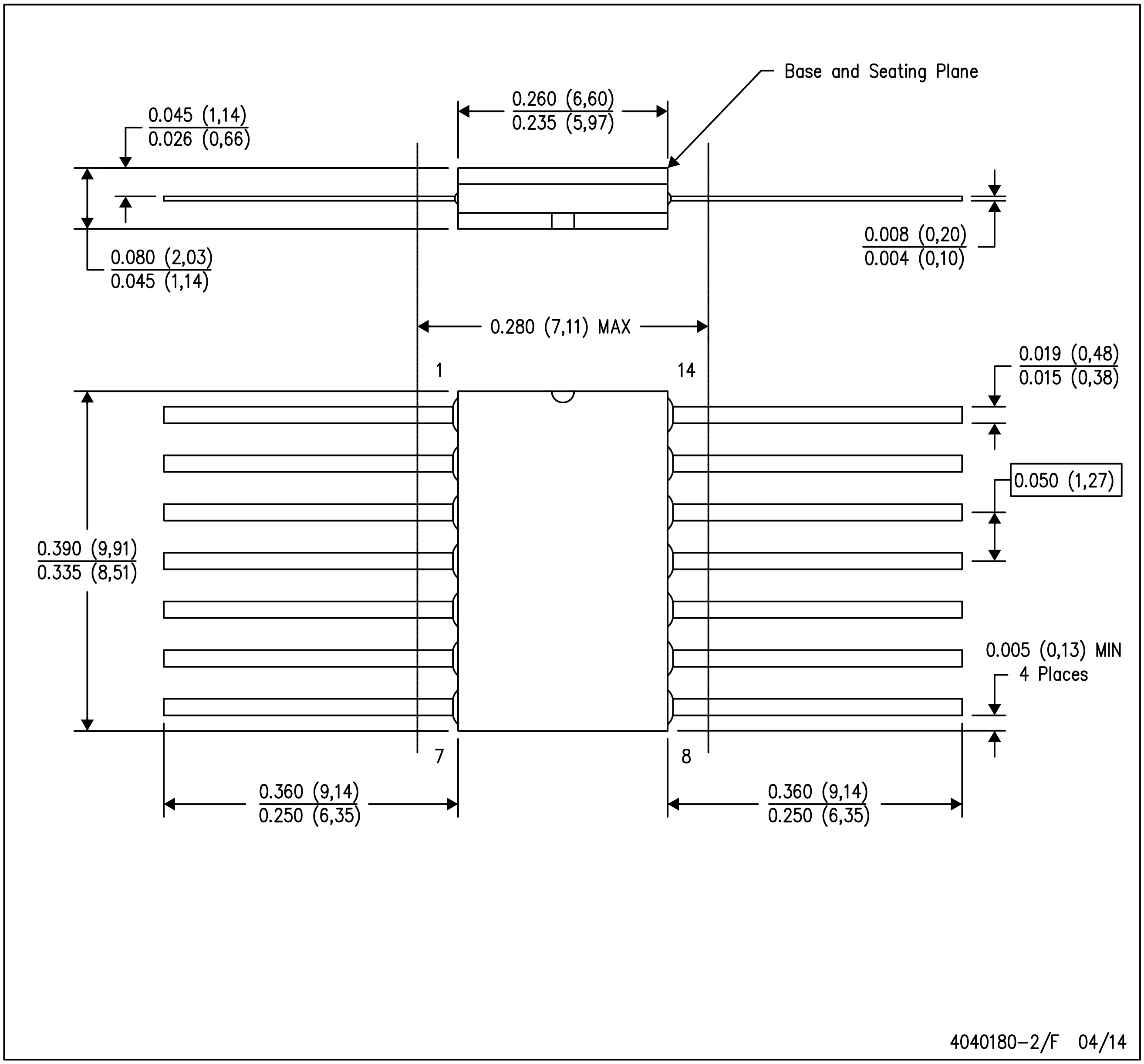


DIM \ PINS **	14	16	20	24
A MAX	10,50	10,50	12,90	15,30
A MIN	9,90	9,90	12,30	14,70

4040062/C 03/03

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.

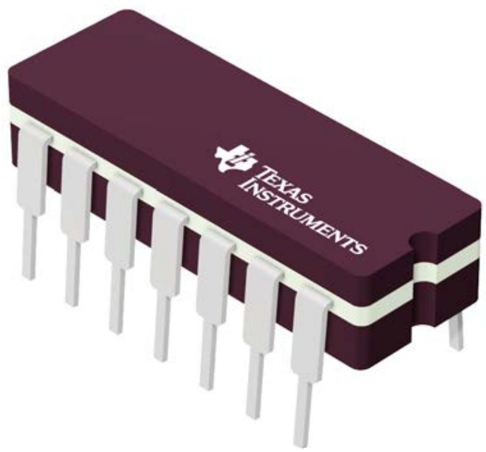
W (R–GDFP–F14) CERAMIC DUAL FLATPACK



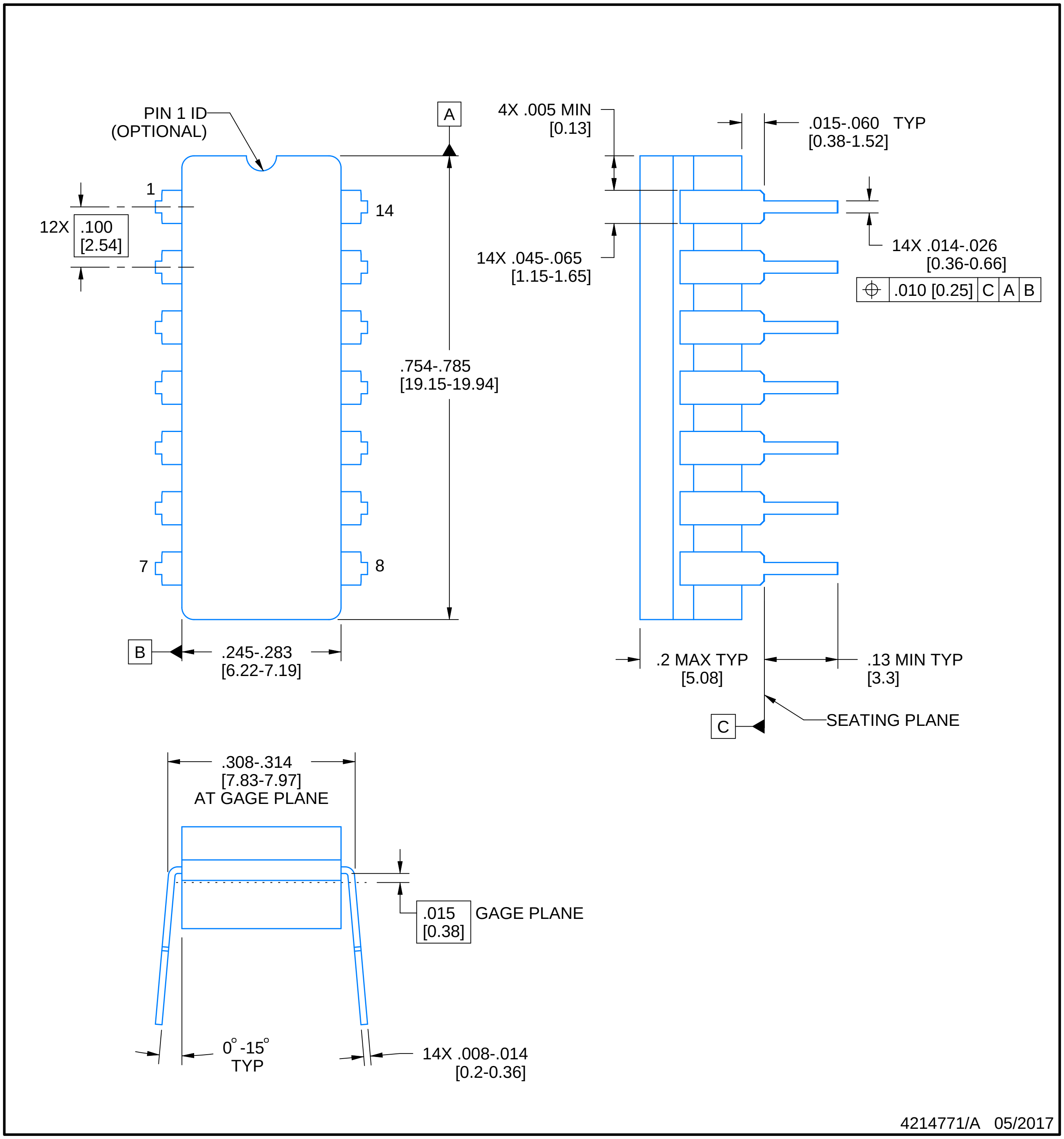
NOTES:
- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only.
- E. Falls within MIL STD 1835 GDFP1–F14

J 14 CDIP - 5.08 mm max height

CERAMIC DUAL IN LINE PACKAGE

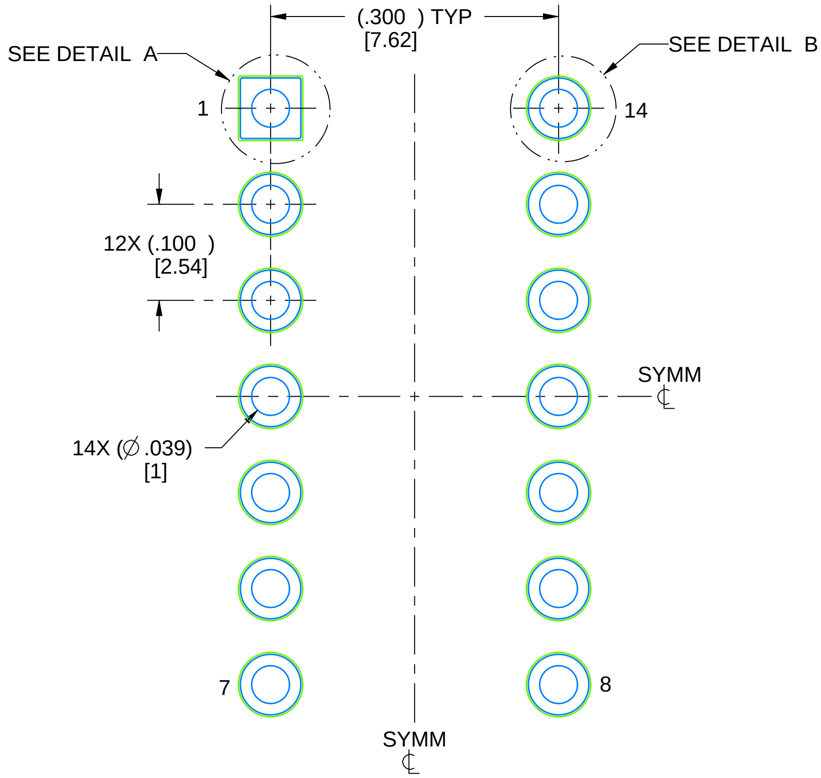


Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

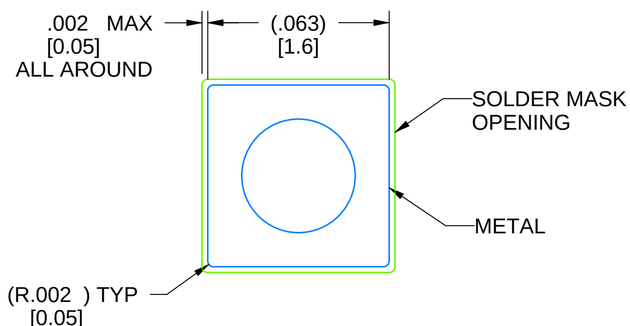


NOTES:

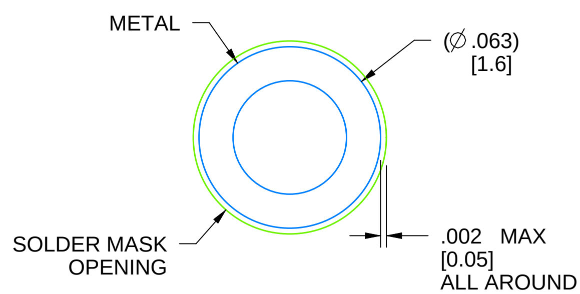
1. All controlling linear dimensions are in inches. Dimensions in brackets are in millimeters. Any dimension in brackets or parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This package is hermitically sealed with a ceramic lid using glass frit.
4. Index point is provided on cap for terminal identification only and on press ceramic glass frit seal only.
5. Falls within MIL-STD-1835 and GDIP1-T14.



LAND PATTERN EXAMPLE
NON-SOLDER MASK DEFINED
SCALE: 5X



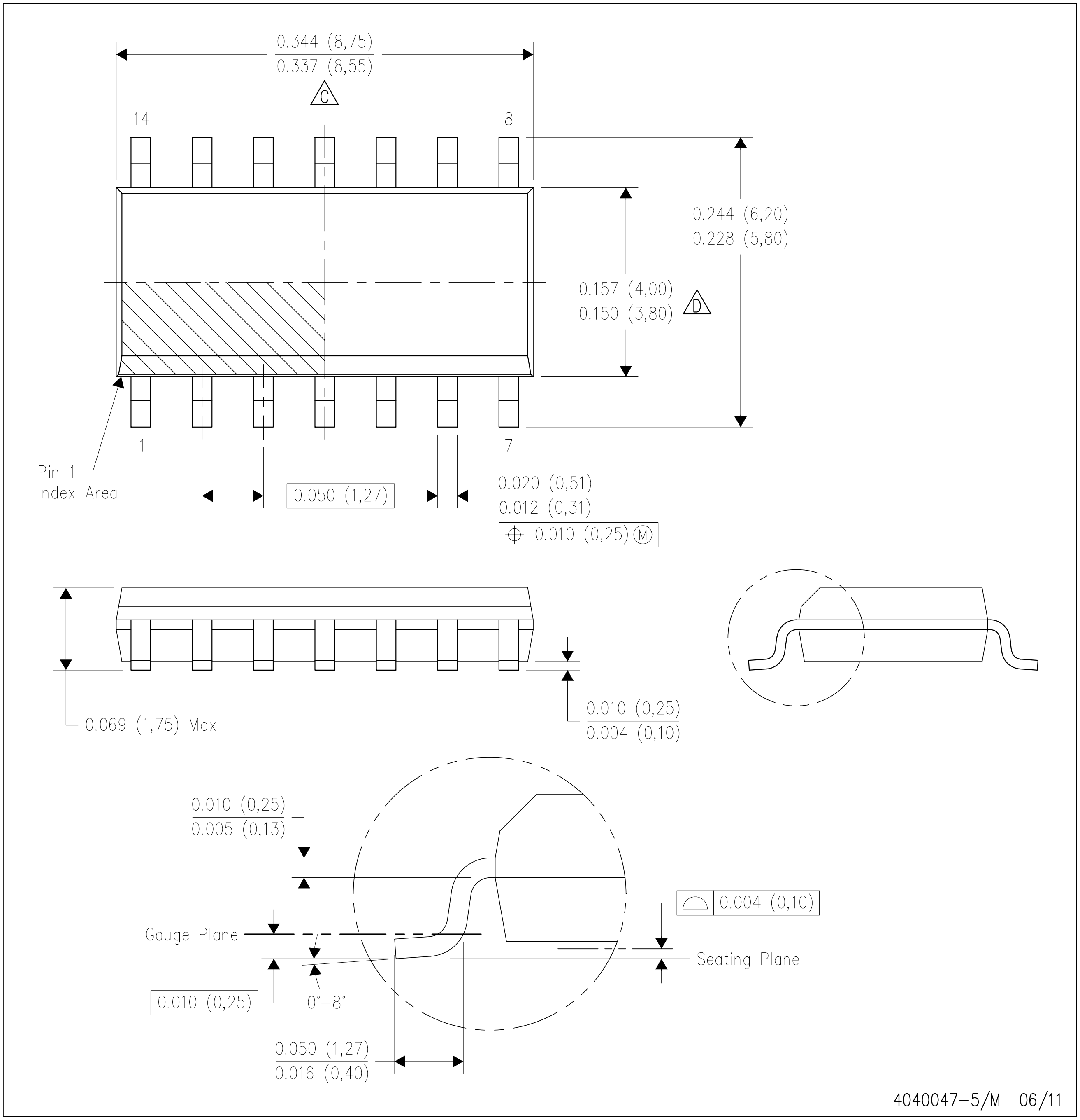
DETAIL A
SCALE: 15X



DETAIL B
13X, SCALE: 15X

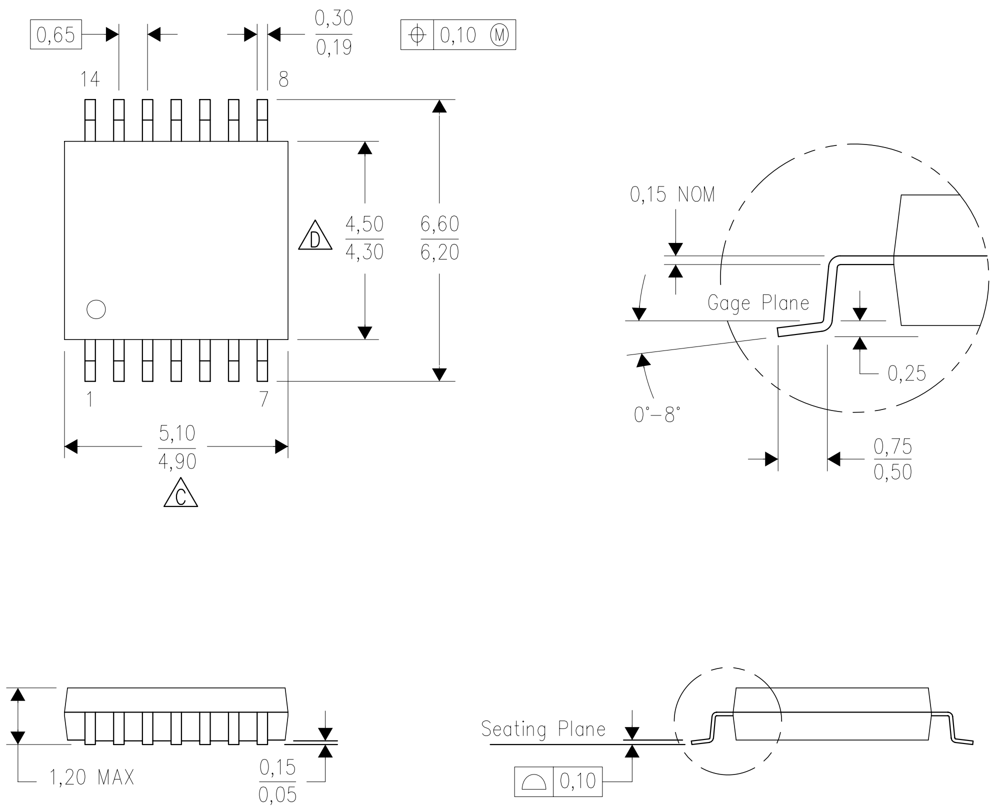
4214771/A 05/2017

D (R–PDSO–G14) PLASTIC SMALL OUTLINE



NOTES:
- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.

PW (R–PDSO–G14) PLASTIC SMALL OUTLINE



4040064–3/G 02/11

NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
- B. This drawing is subject to change without notice.
- C (in a triangle). Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- D (in a triangle). Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO–153

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邮寄地址：上海市浦东新区世纪大道 1568 号中建大厦 32 楼，邮政编码：200122